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(54) LIFETIME MIXED LEVEL NON-VOLATILE MEMORY SYSTEM

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claime

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(51) Int. Cl.

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(Continued)

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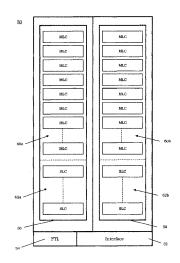
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(57) ABSTRACT

A controller for managing at least one MLC non-volatile memory module and at least one SLC non-volatile memory module. The flash controller is adapted to determine if a range of addresses listed by an entry and mapped to said at least one MLC non-volatile memory module fails a data integrity test. In the event of such a failure, the controller remaps said entry to an equivalent range of addresses of said at least one SLC non-volatile memory module. The flash controller is further adapted to determine which of the blocks in the MLC and SLC non-volatile memory modules are accessed most frequently and allocating those blocks that receive frequent writes to the SLC non-volatile memory module and those blocks that receive infrequent writes to the MLC non-volatile memory module.

10 Claims, 5 Drawing Sheets





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division of application No. 13/455,267, filed on Apr. 25, 2012, now Pat. No. 8,891,298.

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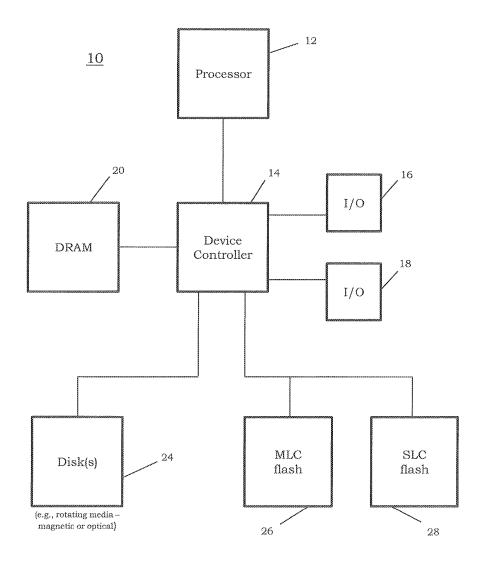
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<u>FIG. 1</u>

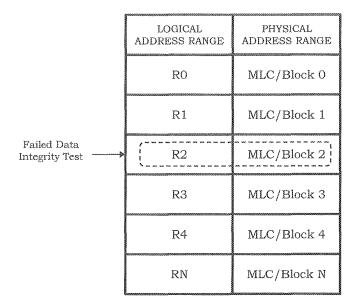


FIG.2A

	LOGICAL ADDRESS RANGE	PHYSICAL ADDRESS RANGE
	R0	MLC/Block 0
	R1	MLC/Block 1
Remapping to SLC flash module	R2	SLC/Block 0
	R3	MLC/Block 3
	R4	MLC/Block 4
	RN	MLC/Block N

FIG.2B

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